Ordering number:EN4501

N-Channel Silicon MOSFET

2SK1849

Ultrahigh-Speed Switching Applications

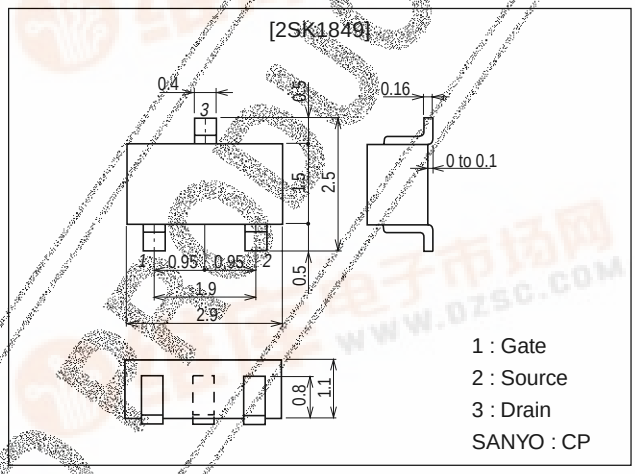
Features

- Low ON resistance.
- Ultrahigh-speed switching.
- Low-voltage drive.

Package Dimensions

unit:mm

2091A



Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		100	V
Gate-to-Source Voltage	V_{GSS}		±15	V
Drain Current (DC)	I_D		250	mA
Drain Current (pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	1	A
Allowable Power Dissipation	P_D		250	mW
Channel Temperature	Tch		150	˚C
Storage Temperature	Tstg		–55 to +150	˚C

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=1mA, V_{GS}=0	100			V
Zero-Gate Votlage Drain Current	I_{DSS}	V_{DS}=100V, V_{GS}=0			100	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±12V, V_{DS}=0			±10	μA
Cutoff Voltage	$V_{GS(off)}$	V_{DS}=10V, I_D=1mA	1.0		2.0	V
Forward Transfer Admittance	$\|yfs\|$	V_{DS}=10V, I_D=150mA	250	500		mS
Static Drain-to-Source On-State Resistance	$R_{DS(on)}1$	I_D=150mA, V_{GS}=10V		2.7	3.5	Ω
	$R_{DS(on)}2$	I_D=150mA, V_{GS}=4V		3.2	4.2	Ω

Marking : MJ

Continued on next page.

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Parameter	Symbol	Conditions	Ratings			Unit
Input Capacitance	Ciss	V_{DS}=20V, f=1MHz		45		pF
Output Capacitance	Coss	V_{DS}=20V, f=1MHz		15		pF
Reverse Transfer Capacitance	Crss	V_{DS}=20V, f=1MHz		3		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit		5		ns
Rise Time	t_r	See specified Test Circuit		10		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit		40		ns
Fall Time	t_f	See specified Test Circuit		35		ns
Diode Forward Voltage	V_{SD}	I_S=250mA, V_{GS}=0		0.9		V

Switching Time Test Circuit